

12

Abstract

Electrostatic clamping of thin wafers in plasma

processing vacuum chambers

Apparatus and methods of processing a substrate having a thickness of
5 250 microns or less are described. Each use a dark space shield between the
plasma in a process chamber and the periphery of the substrate to prevent the
presence of plasma between the shield and the periphery whilst allowing
processing of the substrate. In every case an electrostatic chuck is utilised.

10

15

20